VUTJ003R070NA

Datasheet

VMDSEMI

General Description

$V_{(BR)DSS}$	$R_{DS(ON)_max}$	I_D
30V	7.0mΩ@10V	50A
	11.5mΩ@4.5V	

Symbol

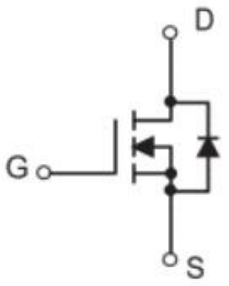
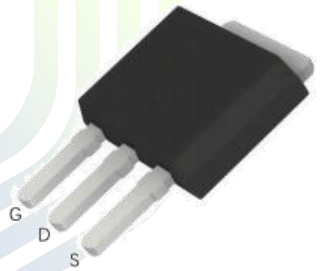


Figure 1 Symbol of VUTJ003R070NA

Features

- Trench Technology Power MOSFET
- Low Gate Charge
- Low Gate Resistance
- Low $R_{DS(ON)}$
- 100% UIS Tested

Package Type



TO-251-3L

Figure 2 Package Type of VUTJ003R070NA

Application

- Power Switch Application
- DC/DC Converter

Ordering Information

Product Name	Package
VUTJ003R070NA	TO-251-3L

Absolute Maximum Ratings (T_A= 25 ºC, unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current Note1	T_C= 25 ºC	I_D	50	A
Continuous Drain Current Note1	T_C= 100 ºC		40	
Continuous Drain Current Note1	T_A= 25 ºC		15	
Pulsed Drain Current Note2		I_{DM}	130	
Avalanche Current Note3		I_{AS}	20	A
Single Pulsed Avalanche Energy Note3		E_{AS}	100	mJ
Total Power Dissipation Note5	T_C= 25 ºC	P_D	35	W
Total Power Dissipation Note5	T_C= 25 ºC		3.5	
Junction Temperature		T_J	150	ºC
Storage Temperature		T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient Note6	$R_{\theta JA}$		35		ºC/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		5		ºC/W

Electrical Characteristics (T_J= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 24V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note4]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	1.6	3.0	V
Static Drain-Source On-Resistance[Note4]	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A		5.5	7.0	mΩ
		V_{GS}=4.5V, I_D= 10A		7.5	11.5	
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=15V		1666		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		222		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		176		pF
Total Gate Charge	Q_g	V_{DS}=15V		15		nC
Gate-Source Charge	Q_{gs}	V_{GS}=4.5V		3.8		
Gate-Drain Charge	Q_{gd}	I_D= 20A		5.5		
Gate Resistance	Rg	f = 1MHz, Open drain		1.48		Ω
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 15V		6		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		10		
Turn-off Delay Time	$t_{d(off)}$	R_L=0.75Ω		16		
Turn-off Fall Time	t_f	R_G=3Ω		4		
Diode Characteristics						
Diode Forward Voltage [Note4]	V_{SD}	V_{GS}=0V, I_S= 10A			1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

3.E_{AS} condition: V_{DD} = 25V,V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.

4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

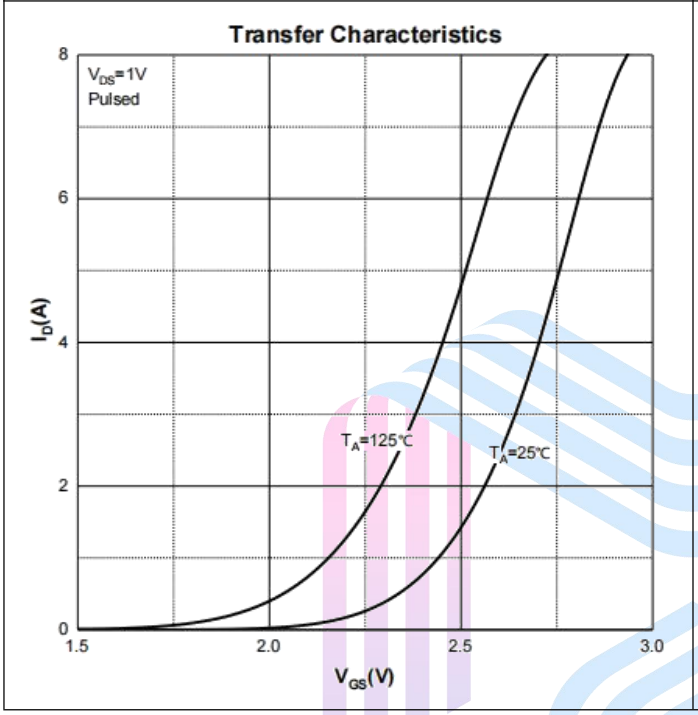


Figure 4: Output Characteristics

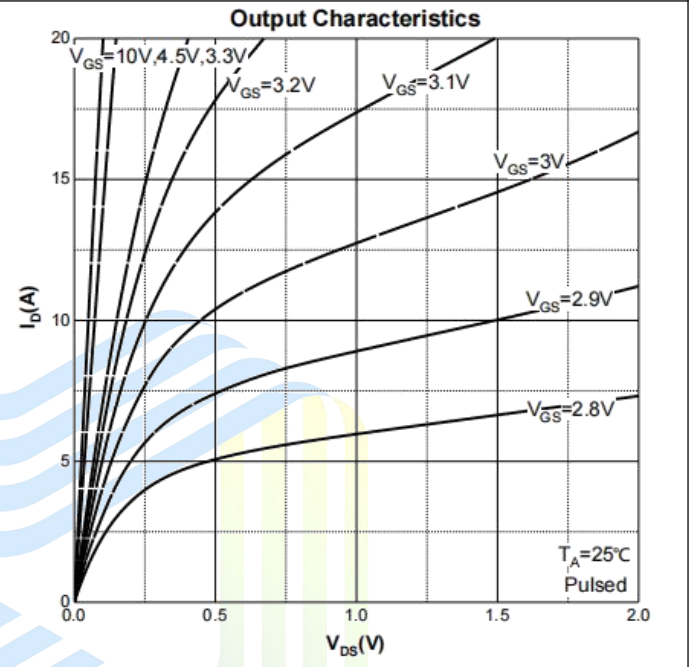


Figure 5: On-Resistance vs. Drain Current

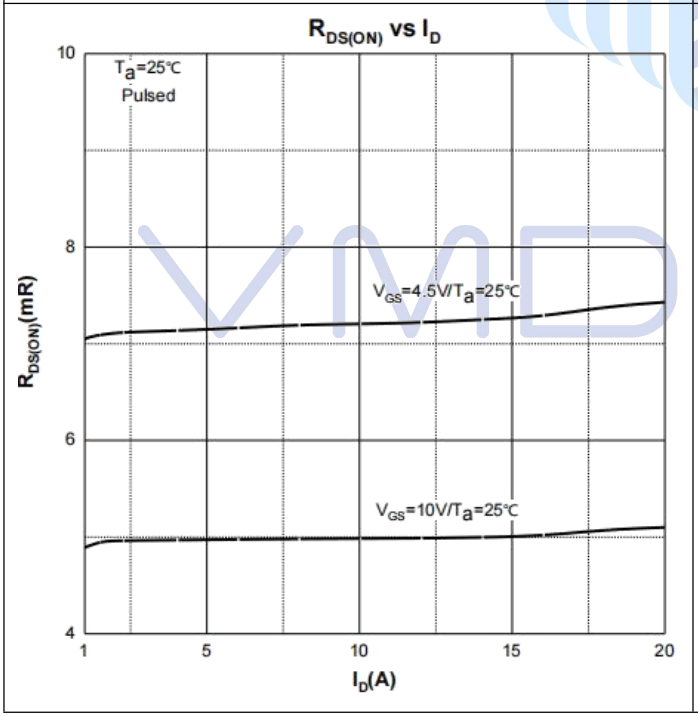


Figure 6: On-Resistance vs. Gate Voltage

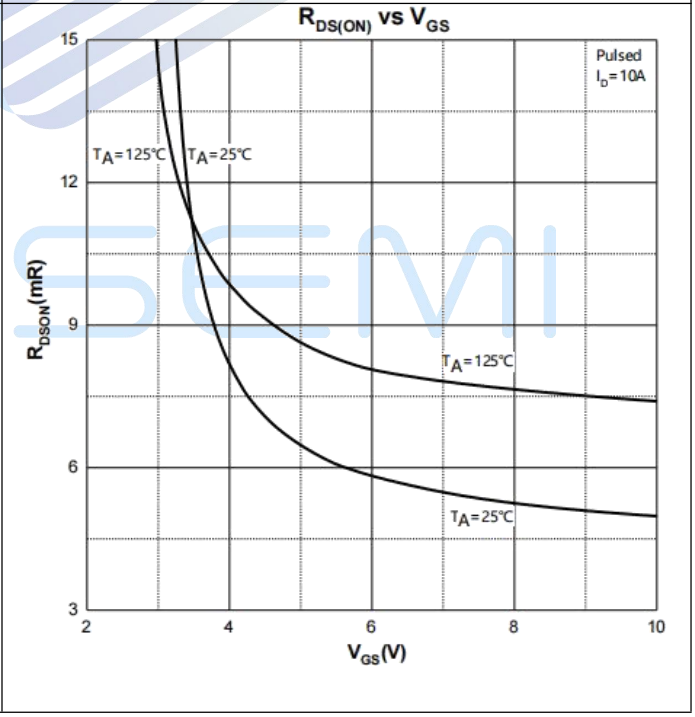


Figure 7: Body Diode Characteristics

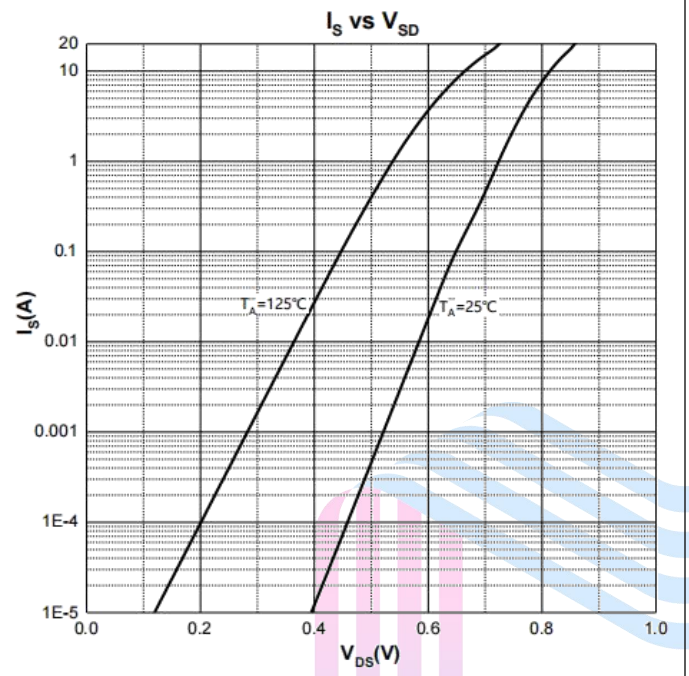


Figure 8: Threshold Voltage

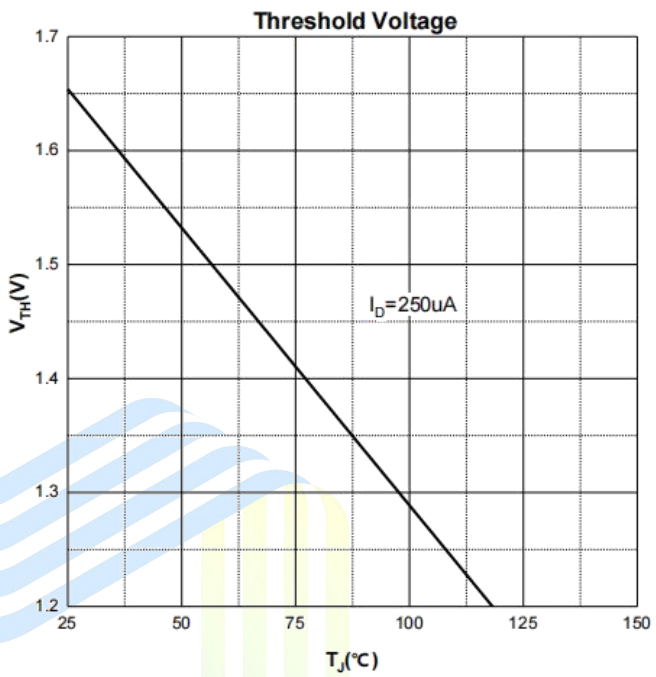


Figure 9: Typical Capacitance

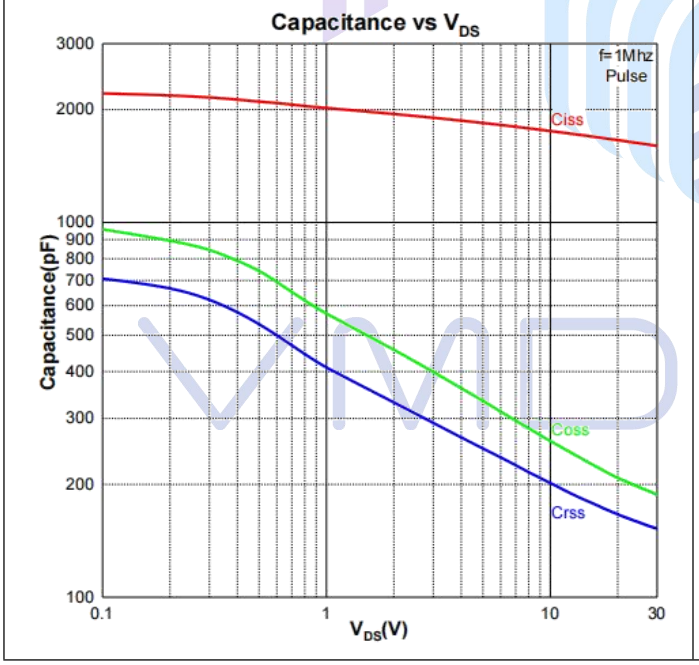


Figure 10: Safe Operating Area

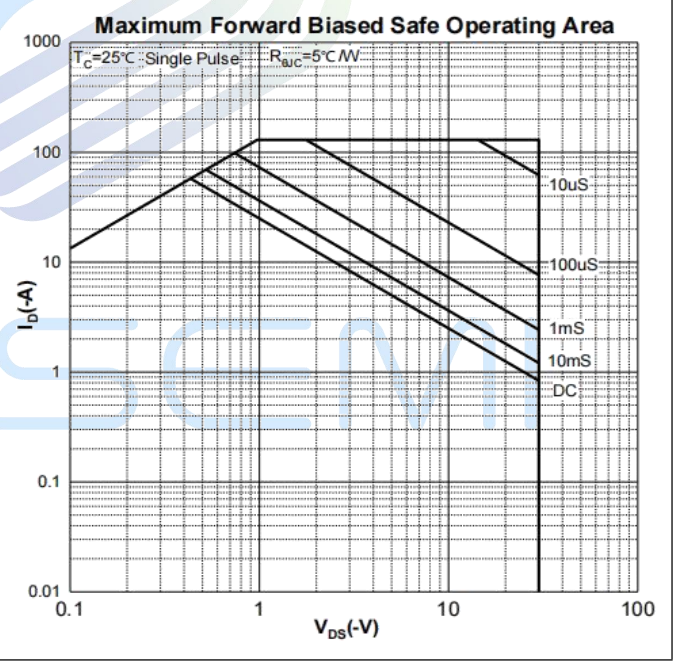
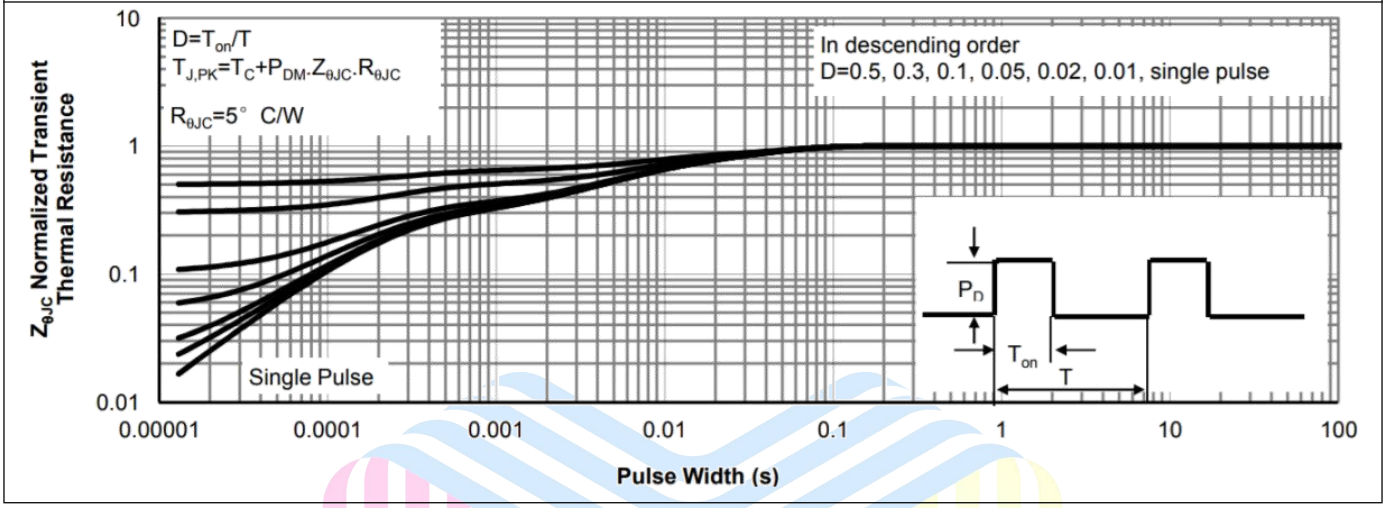


Figure 11: Normalized Maximum Transient Thermal Impedance



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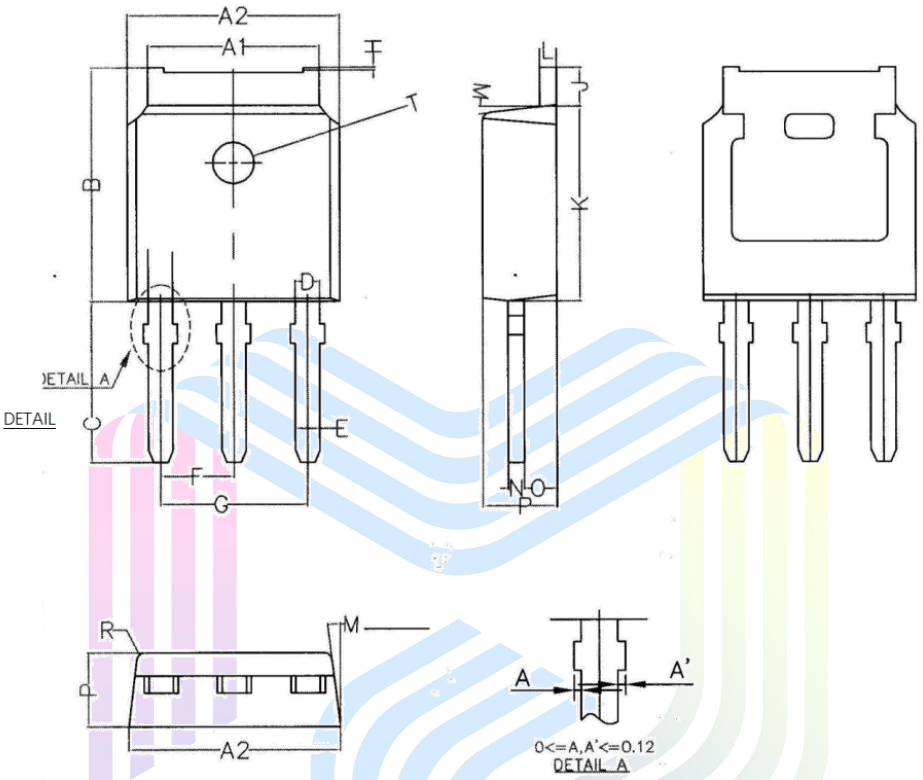
Mechanical Dimensions:

TO-251-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A1	5.220	5.420	0.206	0.213
A2	6.550	6.650	0.258	0.262
B	7.050	7.150	0.278	0.281
C	4.800	5.200	0.189	0.205
D	1.000TYP		0.039TYP	
E	0.760TYP		0.030TYP	
F	2.286TYP		0.090TYP	
G	4.572TYP		0.180TYP	
H	0.150TYP		0.006TYP	
J	0.950	1.050	0.037	0.041
K	6.05	6.15	0.238	0.242
L	0.508TYP		0.020TYP	
M	7°		7°	
N	0.508TYP		0.020TYP	
O	0.960	1.060	0.038	0.042
P	2.250	2.350	0.089	0.093
R	0.25		0.010TYP	

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